



GP 2811
PATENT
AMAT/2966/PDD/KPU1/JW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re Application of: Rath, et al.

Serial No.: 09/165,248

Filed: October 1, 1998

For: A Silicon Carbide Deposition For
Use As A Barrier Layer and An
Etch Stop

Assistant Commissioner of Patents
Washington, D.C. 20231

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Group Art Unit: 2811

Examiner: Unknown

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5/12/00

CERTIFICATE OF MAILING 37 C.F.R. 1.8	
I hereby certify that this correspondence is being deposited on 4/31/00 in the U. S. Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner of Patents, Washington, D. C. 20231.	
4/31/00 Date	D. Brit Nelson D. Brit Nelson

Sir:

PRELIMINARY AMENDMENT

Prior to examination of the above referenced application, the Applicants request that the application be amended as follows:

In the claims:

Please amend the claims as follows:

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23. (Amended) A substrate having a silicon carbide layer deposited thereon, comprising:
- a) a semiconductor substrate;
 - b) a dielectric layer deposited on the substrate; and
 - c) a silicon carbide layer deposited on the dielectric layer and having a dielectric constant of about 6 or less.

REMARKS

The Applicants request that the Examiner enter this Preliminary Amendment prior to examining the case.

Respectfully submitted,

D. Brit Nelson

Registration No. 40,370

THOMASON, MOSER & PATTERSON, L.L.P.

3040 Post Oak Blvd., Suite 1500

Houston, Texas 77056

Telephone: (713) 623-4844

Attorneys for Applicant